

## 1. General description

WSJM65R360B is a high voltage N-channel MOSFET in TO263 package, which utilizes the advanced super-junction technology to provide superior FOM  $R_{DS(on)} * Q_g$  among silicon based MOSFETs. It is particularly suitable for applications require extreme high efficiency and power density.



## 2. Features and benefits

- Superior FOM  $R_{DS(on)} * Q_g$
- Extremely low switching loss
- 100% avalanche tested

## 3. Applications

- PFC stage and/or DC/DC converters in various high efficiency power suppliers, e.g. TV/sever/telecom/lighting power suppliers
- Inverters and motor drives

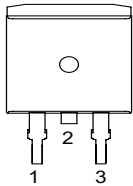
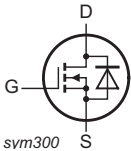
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage			650			V
$V_{GS}$	gate-source voltage			±30			V
$I_D$	continuous drain current	$T_{mb} = 25\text{ °C}$		10			A
$P_{tot}$	power dissipation	$T_{mb} = 25\text{ °C}$		96			W
$T_j$	junction temperature			-55 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$		-	335	360	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 5.5\text{ A}; V_{DS} = 400\text{ V}; V_{GS} = 10\text{ V}$		-	18	-	nC
$E_{OSS}$	coss stored energy	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V}$		-	2.6	-	μJ

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WSJM65R360B	TO263	WSJM65R360BJ	Reel	800	TO263d	17-Mar-2023

## 7. Marking

Table 4. Marking codes

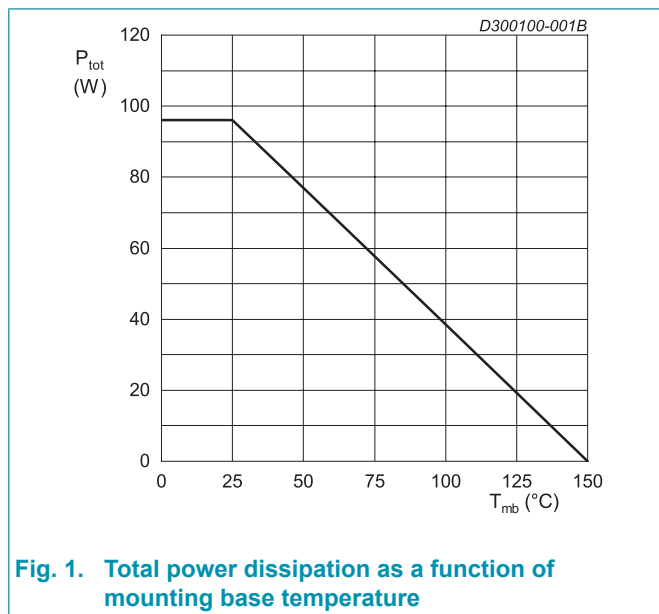
Type number	Marking codes
WSJM65R360B	WSJM 65R360B

## 8. Limiting values

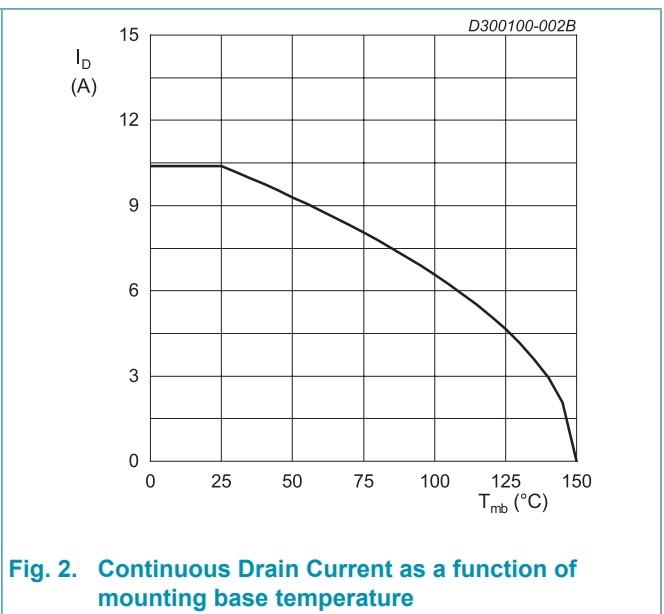
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage			650	V
$V_{GS}$	gate-source voltage			$\pm 30$	V
$I_D$	continuous drain current	$T_{mb} = 25\text{ }^\circ\text{C}$		10	A
		$T_{mb} = 100\text{ }^\circ\text{C}$		6.6	A
$I_{DM}$	pulsed drain current	$T_{mb} = 25\text{ }^\circ\text{C}$		40	A
$P_{tot}$	power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$		96	W
$E_{AS}$	single pulse drain-to-source avalanche	$I_{AS} = 3.3\text{ A}$ ; $R_{GS} = 25\text{ }\Omega$ ; $V_{DD} = 50\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		54	mJ
$E_{AR}$	repetitive avalanche energy	$I_{AS} = 3.3\text{ A}$ ; $R_{GS} = 25\text{ }\Omega$ ; $V_{DD} = 50\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$		0.6	mJ
$I_{AS}$	avalanche current, single pulse			3.3	A
dv/dt	MOSFET dv/dt ruggedness			50	V/ns
dv/dt	reverse diode dv/dt			15	V/ns
dI <sub>r</sub> /dt	maximum diode commutation speed			500	A/ $\mu$ s
$T_{stg}$	storage temperature			-55 to 150	$^\circ\text{C}$
$T_j$	junction temperature			-55 to 150	$^\circ\text{C}$



**Fig. 1. Total power dissipation as a function of mounting base temperature**

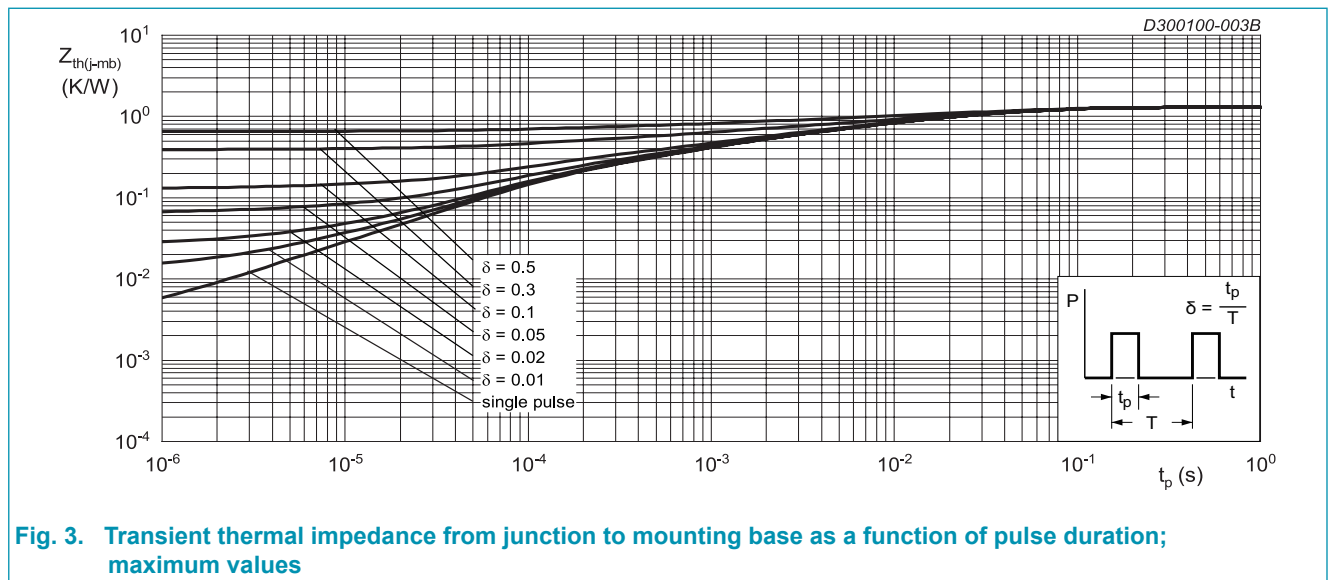


**Fig. 2. Continuous Drain Current as a function of mounting base temperature**

## 9. Thermal & Mechanical characteristics

**Table 6. Thermal & Mechanical characteristics**

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.97	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

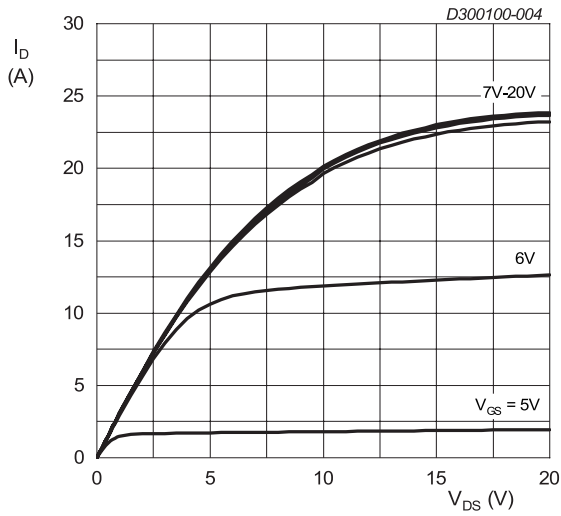


**Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values**

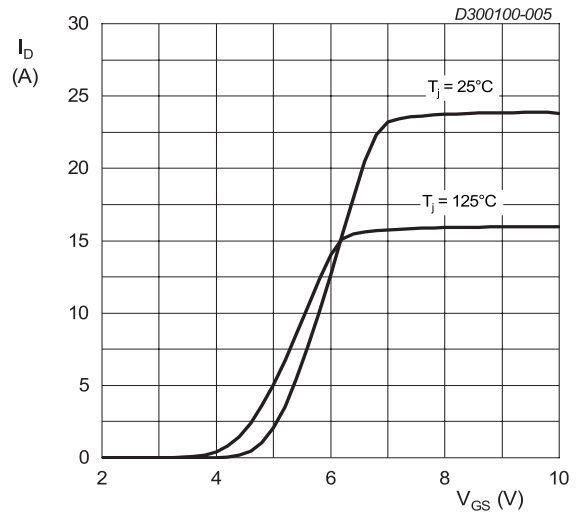
## 10. Characteristics

**Table 7. Characteristics**
 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise noted

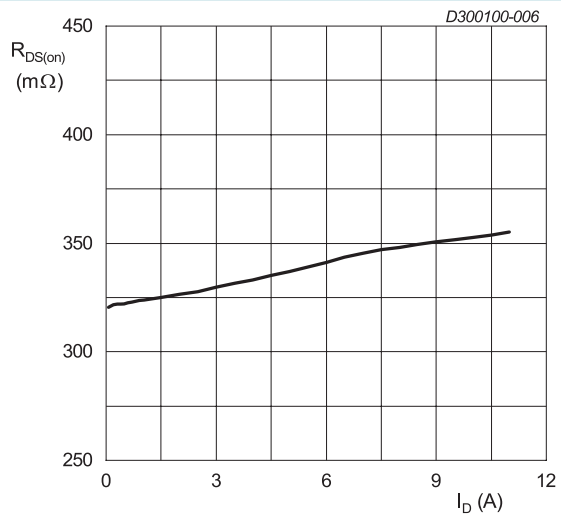
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}$		650	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\ \mu\text{A}; V_{DS} = V_{GS}$		2.5	-	4.5	V
$I_{DSS}$	drain leakage current	$V_{DS} = 650\ \text{V}; V_{GS} = 0\ \text{V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 650\ \text{V}; V_{GS} = 0\ \text{V}; T_j = 125\text{ }^\circ\text{C}$		-	-	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 30\ \text{V}; V_{DS} = 0\ \text{V}$		-	-	$\pm 100$	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}; I_D = 5.5\ \text{A}$		-	335	360	m $\Omega$
$R_G$	gate resistance	$f = 1\ \text{MHz}$		-	18	-	$\Omega$
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 5.5\ \text{A}; V_{DS} = 400\ \text{V}; V_{GS} = 10\ \text{V}$		-	18	-	nC
$Q_{GS}$	gate-source charge			-	4.1	-	nC
$Q_{GD}$	gate-drain charge			-	7.0	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 400\ \text{V}; V_{GS} = 0\ \text{V}; f = 1\ \text{MHz}$		-	808	-	pF
$C_{oss}$	output capacitance			-	23	-	pF
$C_{rss}$	reverse transfer capacitance			-	1.8	-	pF
$C_{o(er)}$	effective output capacitance, energy related	$V_{GS} = 0\ \text{V}; V_{DS} = 0\ \text{to}\ 400\ \text{V}$		-	33	-	pF
$C_{o(tr)}$	effective output capacitance, time related			-	148	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 400\ \text{V}; V_{GS} = 10\ \text{V}; R_G = 2\ \Omega;$ $I_D = 5.5\ \text{A}$		-	30	-	ns
$t_r$	rise time			-	9.6	-	ns
$t_{d(off)}$	turn-off delay time			-	52	-	ns
$t_f$	fall time			-	14	-	ns
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$V_{GS} = 0\ \text{V}; I_S = 5.5\ \text{A}$		-	0.8	1.1	V
$I_S$	body-diode continuous current	$T_{mb} = 25\text{ }^\circ\text{C}$		-	-	10	A
$t_{rr}$	reverse recovery time	$V_R = 400\ \text{V}; I_F = 5.5\ \text{A}; di_F/dt = 100\ \text{A}/\mu\text{s}$		-	229	-	ns
$Q_{rr}$	reverse recovered charge			-	2.3	-	$\mu\text{C}$
$I_{rrm}$	reverse recovery current			-	20	-	A



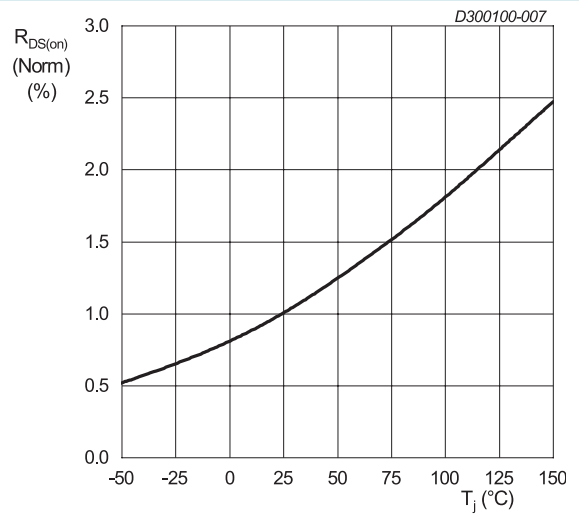
**Fig. 4. Drain current as a function of drain-source voltage; typical values**



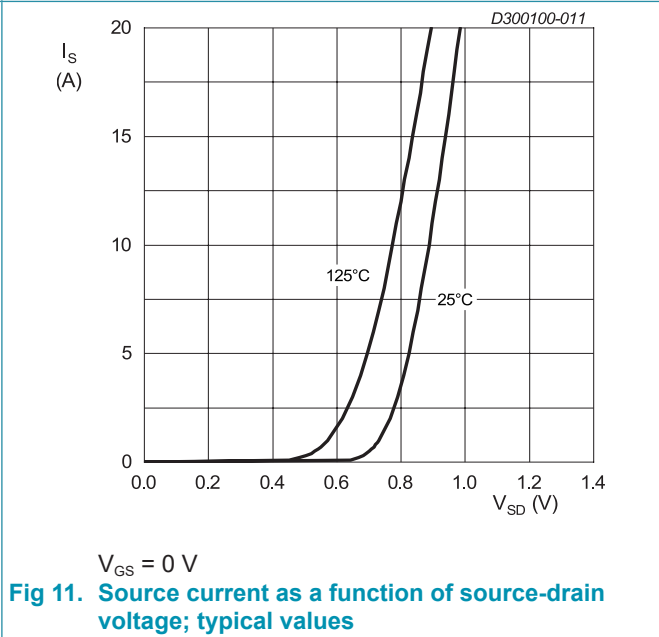
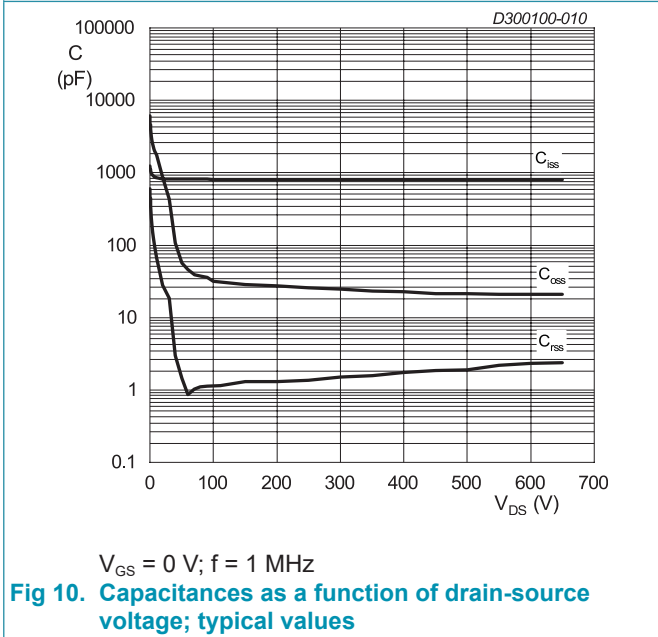
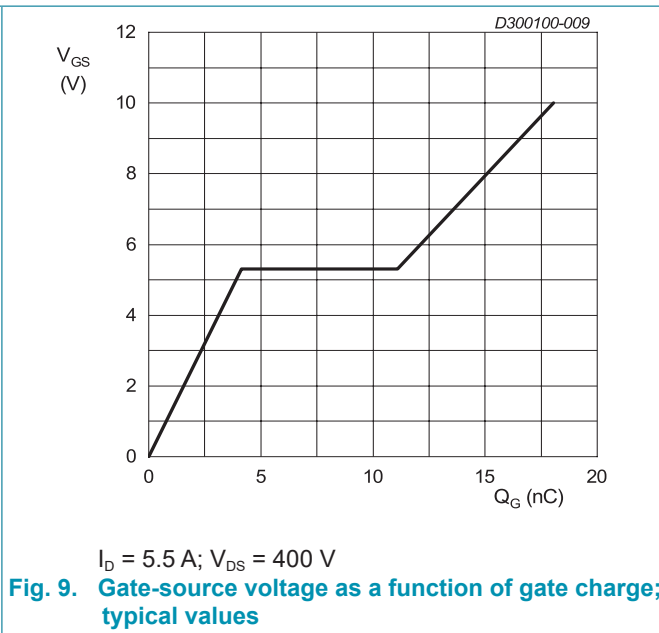
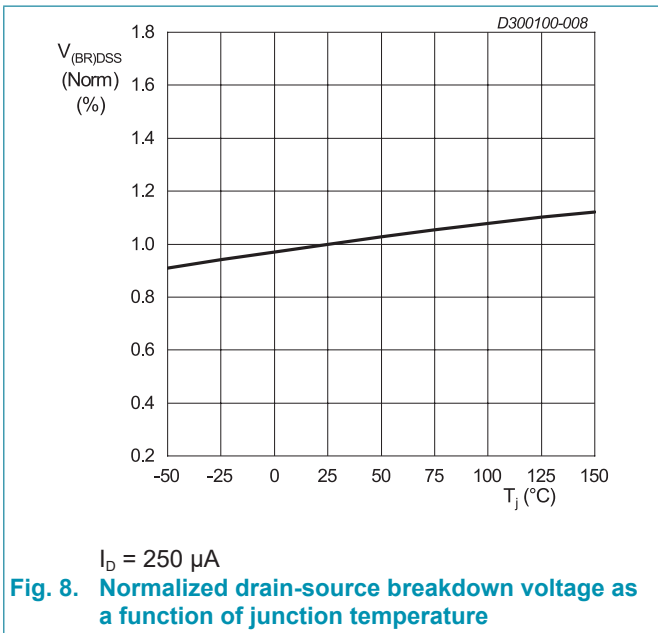
$V_{DS} = 20\text{ V}$   
**Fig. 5. Drain current as a function of gate-source voltage; typical values**

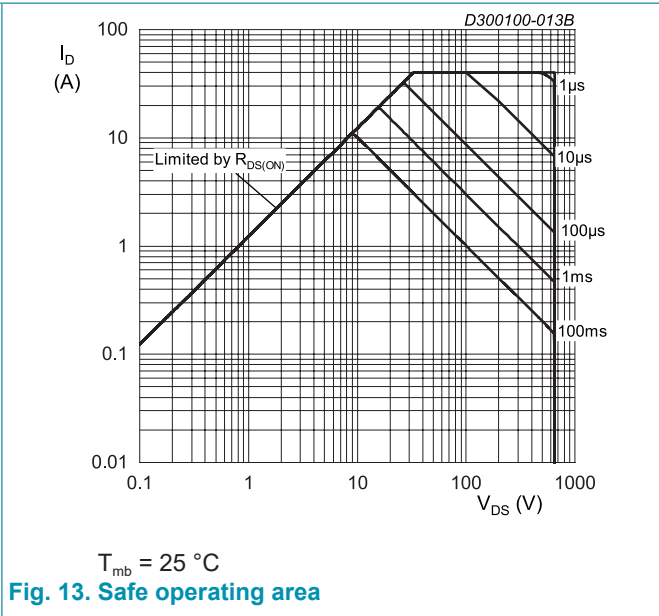
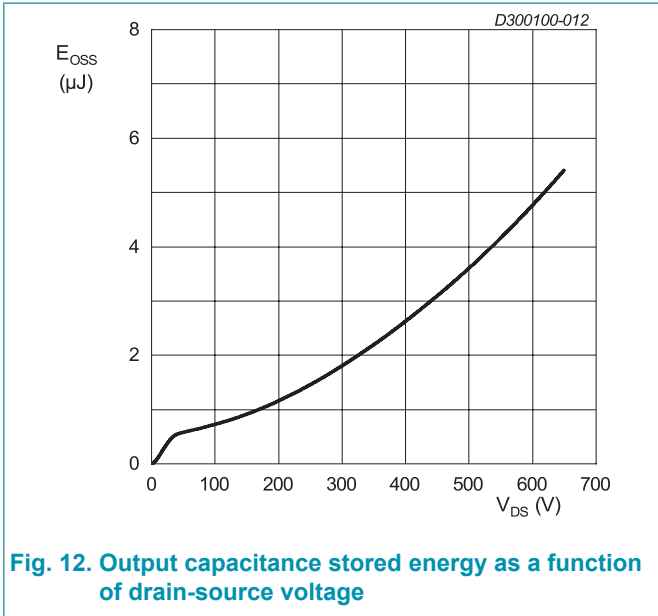


$V_{GS} = 10\text{ V}$   
**Fig. 6. Drain-source on-state resistance as a function of drain current; typical values**



$V_{GS} = 10\text{ V}; I_D = 5.5\text{ A}$   
**Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature**



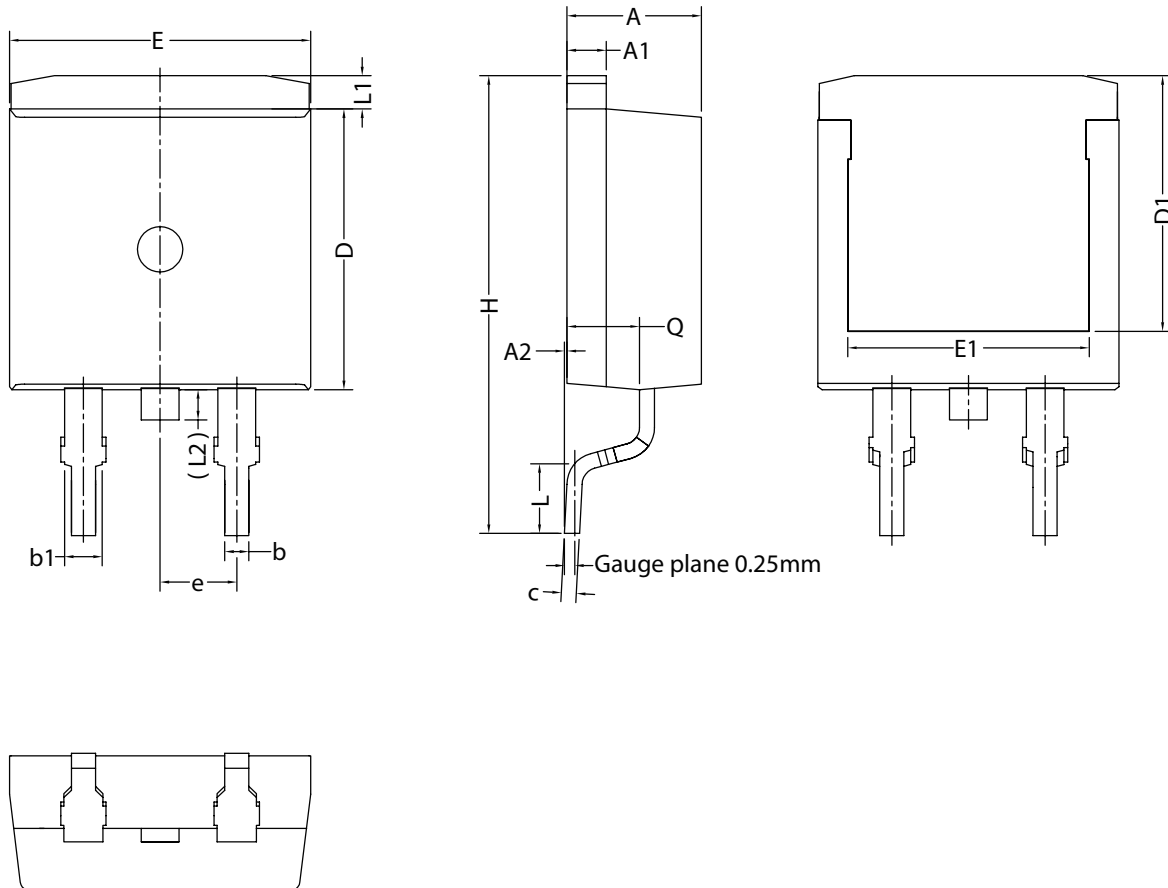




### 11. Package outline

Plastic single-ended surface-mounted package (D2PAK);

TO263



Note:  
All dimensions do not include mold flash or protrusion.

Unit	A	A1	A2	b	b1	c	D	D1	e	E	E1	H	L	L1	L2	Q
MM	min	4.30	1.27	0.00	0.75	1.20	0.45	9.00	7.65	9.85	7.80	14.84	1.90	0.90	--	2.20
	max	4.60	1.37	0.25	0.90	1.36	0.60	9.45	8.05	10.10	8.20	15.64	2.60	1.35	1.50	2.40

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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